

ABSTRACT OF THE DISCLOSURE

A magnetic random access memory is provided including a substrate, a magnetoresistance element which includes a ferromagnetic layer having an invertible spontaneous magnetization, which varies in resistance according to the direction of the spontaneous magnetization, and is formed above the substrate, and a wiring which extends in a first direction and is used for making an electric current flow to generate a magnetic field to be applied to the magnetoresistance element. The wiring is formed so as to pass through a first position which is closer to the substrate than the magnetoresistance element and does not overlap the magnetoresistance element when viewed from a direction perpendicular to the main surface of the substrate, and a second position being above said magnetoresistance element.